

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions and listings of claims in the application:

1. - 5. (Canceled)

6. (Currently Amended) A semiconductor device having a lateral high-breakdown-voltage transistor comprising:

a first-conductivity-type semiconductor layer;

a second-conductivity-type source region formed in the semiconductor layer;

a second-conductivity-type drain region formed in or outside the semiconductor layer, separated from the source region;

a gate electrode formed above the semiconductor layer between the drain region and the source region, insulated from the semiconductor layer;

a second-conductivity-type drain contact region formed in the drain region and having a higher impurity concentration than the drain region;

a drain wiring electrically connected to the drain region via the drain contact region, and having a first contact surface being in contact with the drain contact region;

a first-conductivity-type substrate contact region formed adjacent to the source region; and

a source wiring electrically connected to the source region, and also connected to the semiconductor layer via the substrate contact region, and having a second contact surface being in contact with the source region and the substrate contact region,

wherein:

the drain contact region has a first distance from the first contact surface to an edge of the drain contact region facing the source region,

the source region has a second distance from the second contact surface to an edge of the source region facing the drain region, and

of the first and second distances, only the first distance is 5  $\mu\text{m}$  or more  
~~a distance from a contact surface of the drain wiring and the drain contact region to an edge of the source region side of the drain contact region being 5  $\mu\text{m}$  or more.~~

7. - 18. (Canceled)

19. (Previously Presented) The semiconductor device having the lateral high-breakdown-voltage transistor according to claim 6, further comprising a diode formed by short-circuiting the source wiring and the gate electrode.

20. (Canceled)

21. (New) The semiconductor device according to claim 6, wherein the substrate contact region extends from inside the second contact surface to outside the second contact surface along a surface of the semiconductor layer.